

# **HL6740FG**

# **Dual Beam Visible Laser Diode**

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## **Description**

The HL6740FG is a  $0.67~\mu m$  band AlGaInP laser diode with a multi-quantum well (MQW) structure. It is an array of two individual beams on one chip. Therefore, it is suitable as a light source for a high-speed printer, such as PPC and LBP, and so on.

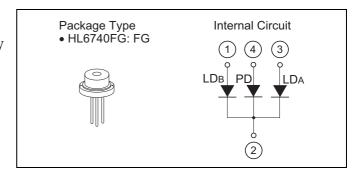
#### **Features**

• Continuous operating output to each beam: 5 mW CW

• Visible light output: 675 nm Typ

• Difference of wavelength between 2 beams : 3 nm Max

• Low threshold current: 35 mA Typ



## **Absolute Maximum Ratings**

 $(T_C = 25^{\circ}C)$ 

Item	Symbol	Ratings	Unit
Optical output power	Po	5	mW
Pulse optical output power	P <sub>O(pulse)</sub>	6*	mW
LD reverse voltage	$V_{R(LD)}$	2	V
PD reverse voltage	$V_{R(PD)}$	30	V
Operating temperature	Topr	-10 to +50	°C
Storage temperature	Tstg	-40 to +85	°C

Note: Pulse condition : Pulse width  $\leq 1 \mu s$ , duty  $\leq 50\%$ 

## **Optical and Electrical Characteristics**

 $(T_C = 25^{\circ}C)$ 

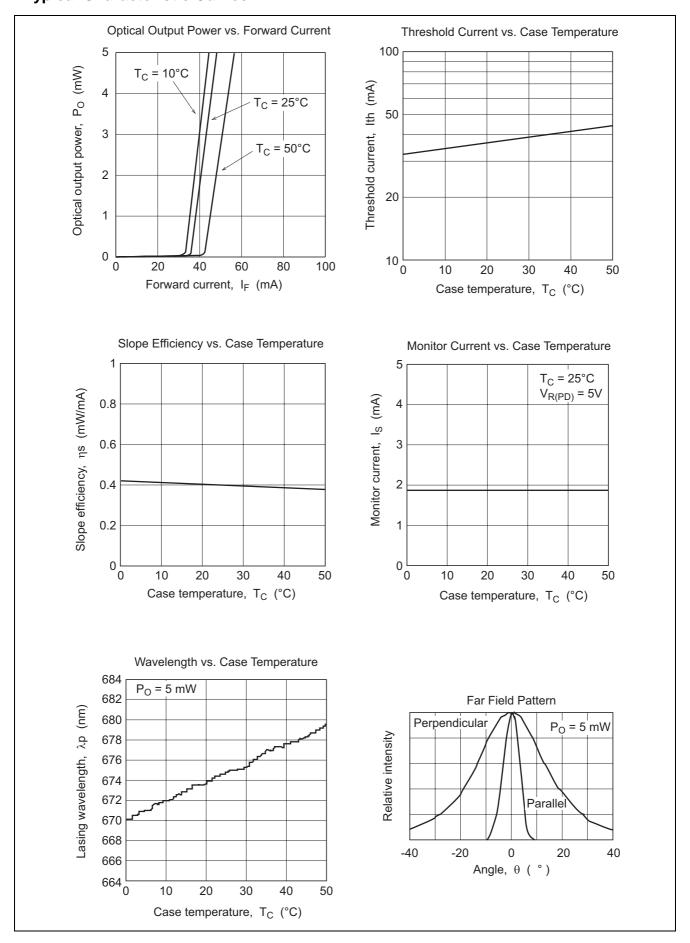
Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Threshold current	Ith	_	35	50	mA	_
LD Operating current	I <sub>OP</sub>	_	_	75	mA	$P_0 = 5 \text{ mW}$
LD Operating voltage	V <sub>OP</sub>	_	2.3	2.7	V	$P_0 = 5 \text{ mW}$
Slope efficiency	ης	0.2	0.4	0.6	mW/mA	$3 \text{ (mW)} / (I_{(4\text{mW})} - I_{(1\text{mW})})$
Beam divergence parallel to the junction	θ//	6.5	8	11	0	P <sub>O</sub> = 5 mW
Beam divergence perpendicular to the junction	θΤ	20	30	36	o	P <sub>O</sub> = 5 mW
Lasing wavelength	λр	665	675	680	nm	$P_0 = 5 \text{ mW}$
Difference of wavelength *2	Δλρ	_	_	3.0	nm	$P_0 = 5 \text{ mW}$
Monitor current	Is	1.0	_	4.0	mA	$P_0 = 5 \text{ mW}, V_{R(RD)} = 5V$

Notes: 1. The characteristics are specified under the condition of a single beam operation unless otherwise specified.

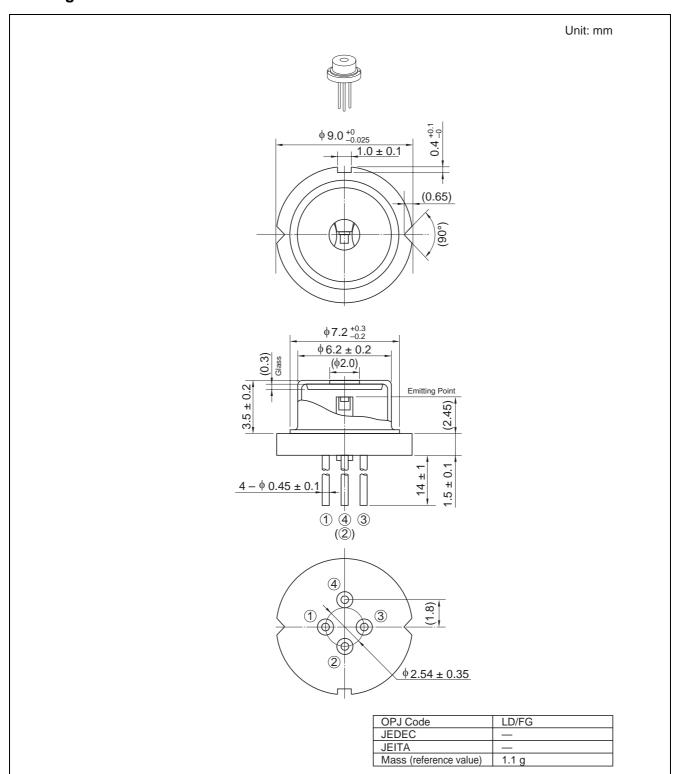
2.  $\Delta\lambda p$  is specified as absolute value of the difference between two beams operated every beam.



## **Typical Characteristic Curves**



# **Package Dimensions**



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#### **Sales Offices**



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